

LIST OF REFERENCES CITED BY APPLICANT
 (Use several sheets if necessary)

ATTY DOCKET NO.

60889-5001

APPLICATION NO

To be assigned

APPLICANT

Liu and Gregoire

FILING DATE

Herewith

GROUP

To be assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RL	US 2001/0017390 A1	08/30/01	Long et al. (published application no. 09/808,896)	257	368	
	US 2002/0011635 A1	01/2002	Abe et al.	257	408	
	5,449,937	09/1995	Arimura et al.	257	345	
	5,614,752	03/1997	Takenaka, Kazuhiro	257	408	
	5,920,104	07/1999	Nayak et al.	257	408	
	6,081,010	06/2000	Sanchez, Julian J.	257	345	
	6,147,377	11/14/2000	Liu	257	314	
	6,147,383	11/2000	Kuroda, Hideaki	257	344	
	6,258,683	07/10/2001	Besser et al.	438	306	
	6,265,256	07/24/2001	An et al.	438	201	
	6,285,054	09/04/2001	Liu et al.	257	315	

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

RL	Lee, W., Hwang, H., "Hot Carrier Degradation for Narrow Width MOSFET with Shallow Trench Isolation," Microelectronics Reliability, Received 07/13/1999, Revised 09/22/1999, 40 (2000), pp. 49-56

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.